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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

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In re the patent of:

KONNO et al.

Patent Number: 5,397,432

Issued: March 14, 1995

For: METHOD FOR PRODUCING SEMICONDUCTOR INTEGRATED CIRCUITS AND
APPARATUS USED IN SUCH METHOD

REQUEST FOR CERTIFICATE OF CORRECTION

Assistant Commissioner
for Patents

Washington, D.C. 20231

March 10, 1997

Sir:

CERTIFICATE

APR 18 1997

The undersigned requests that a Certificate of Correction be issued for the
above-identified patent as indicated on the attached Form PTO-1050.

REMARKS

This request is being made in order to correct our typographical error in
column 11, line 39 and the omission of symbols in Table-1. In support of the corrections
to Table-1, we are enclosing a copy of page 24 of the specification.

It is respectfully submitted that no new matter has been added.

Enclosed is a check for One Hundred Dollars (\$100.00) to cover any
necessary cost for this change. If however, any additional fees are due, please charge our
Deposit Account No. 14-1060.

Respectfully submitted,

NIKAIDO, MARMELSTEIN, MURRAY & ORAM LLP

George E. Oram, Jr.

Reg. No. 27,931

Atty. Case No. P698-1333

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Enclosures: PTO Form 1050; Copy of Page 24 of the Specification; Check # 12856



Table 1

Conditions	Amount of residual chlorine $\mu\text{m g/cm}^2$ 10^{15}atoms/cm^2		After-corrosion	Symbols shown in Fig. 9
① Etching only	0.92 ± 0.06	16.0 ± 1.0	Large	○
② Downflow ashing using O_2 after ①	0.89 ± 0.06	15.5 ± 1.0	Large	●
③ Downflow ashing using $\text{O}_2 + \text{CF}_4$ after ①	0.54 ± 0.03	9.3 ± 0.4	Small	■
④ Downflow ashing using $\text{O}_2 + \text{H}_2\text{O}$ after ①	0.23 ± 0.03	4.0 ± 0.5	No	◇
⑤ Exposure to H_2O after ② (30sec)	0.51 ± 0.02	8.7 ± 0.3	Small	▲
⑥ Exposure to H_2O after ② (90sec)	0.48 ± 0.01	8.1 ± 0.2	Small	▲
⑦ Exposure to H_2O after ② (180sec)	0.45 ± 0.04	7.6 ± 0.7	Small	▲
⑧ Downflow treatment using H_2O after ② (30sec)	0.28 ± 0.01	4.7 ± 0.2	None	△
⑨ Downflow treatment using H_2O after ② (90sec)	0.15 ± 0.00	2.5 ± 0.0	No	△
⑩ Downflow treatment using H_2O after ② (180sec)	0.11 ± 0.01	1.9 ± 0.1	No	△
⑪ Downflow treatment using H_2 after ② (30sec)	0.68 ± 0.01	11.8 ± 0.2	Small	▼
⑫ Downflow treatment using H_2O after ② (90sec)	0.68 ± 0.01	11.7 ± 0.1	Small	▼
⑬ Downflow treatment using H_2 after ② (180sec)	0.64 ± 0.01	11.1 ± 0.2	Small	▼

Exposure to H_2O : heated at 120°C in water vapor at 0.1 Torr.

UNITED STATES PATENT AND TRADEMARK OFFICE
CERTIFICATE OF CORRECTION

PATENT NO. : 5,397,432
DATED : March 14, 1995
INVENTOR(S) : KONNO et al.

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Column 11, line 39, delete "or" insert therefor -- and -- *A*

5,397,432

MAILING ADDRESS OF SENDER:

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It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Table - 1 insert symbols

Conditions	Amount of residual chlorine umg/cm ² · 10 ¹⁵ atoms/cm ²	After- corrison	Symbols shown in FIG. 9
① Etching only	0.92±0.06	16.0±1.0	Large ○
② Downflow ashing using O ₂ after ①	0.39±0.06	15.5±1.0	Large ●
③ Downflow ashing using O ₂ +CF ₄ after ①	0.54±0.03	9.3±0.4	Small ■
④ Downflow ashing using O ₂ +H ₂ O after ①	0.23±0.03	4.0±0.5	No ◇
⑤ Exposure to H ₂ O after ② (30sec)	0.51±0.02	8.7±0.3	Small ▲
⑥ Exposure to H ₂ O after ② (90sec)	0.48±0.01	8.1±0.2	Small ▲
⑦ Exposure to H ₂ O after ② (180sec)	0.45±0.04	7.6±0.7	Small ▲
⑧ Downflow treatment using H ₂ O after ② (30sec)	0.29±0.01	4.7±0.2	None Δ
⑨ Downflow treatment using H ₂ O after ② (90sec)	0.15±0.00	2.5±0.0	No Δ
⑩ Downflow treatment using H ₂ O after ② (180sec)	0.11±0.01	1.9±0.1	No Δ
⑪ Downflow treatment using H ₂ after ② (30sec)	0.68±0.01	11.8±0.2	Small ▼
⑫ Downflow treatment using H ₂ O after ② (90sec)	0.68±0.01	11.7±0.1	Small ▼
⑬ Downflow treatment using H ₂ after ② (180sec)	0.64±0.01	11.1±0.2	Small ▼

Exposure to H₂O: heated at 120° C. in water vapor at 0.1 Torr.

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Conditions	Amount of residual chlorine umg/cm ² 10 ¹⁵ atoms/cm ²		After- corrosion	Symbols shown in FIG. 9
① Etching only	0.32±0.06	16.0±1.0	Large	○
② Downflow ashing using O ₂ after ①	0.39±0.06	15.5±1.0	Large	●
③ Downflow ashing using O ₂ +CF ₄ after ①	0.54±0.03	9.3±0.4	Small	■
④ Downflow ashing using O ₂ +H ₂ O after ①	0.23±0.03	4.0±0.5	No	◇
⑤ Exposure to H ₂ O after ② (30sec)	0.51±0.02	8.7±0.3	Small	▲
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